

## N-Channel 100 V (D-S) Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ (m $\Omega$ )(Typ.)	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
100	85 at $V_{GS} = 10$ V	3.1	3.49 nC

### FEATURES

- DT-Trench Power MOSFET
- Low on-resistance
- SuperLow Gate Charge

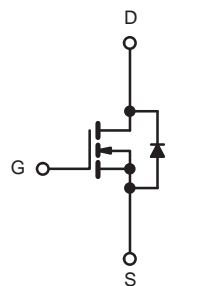
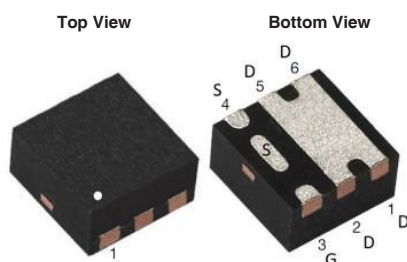
### APPLICATIONS

- Load Switch
- PWM Applications
- Power Management



**RoHS**  
COMPLIANT

### DFN1.6X1.6-6L Pin Configuration



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$T_A = 25$ °C	$I_D$	A
	$T_A = 70$ °C	3.1	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	12	W
Maximum Power Dissipation <sup>c</sup>	$T_A = 25$ °C	$P_D$	
	$T_A = 70$ °C	1.8 <sup>c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	°C
Soldering Recommendations (Peak Temperature)		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>d</sup>	$R_{thJA}$	-	70	°C/W

#### Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
- The value of  $R_{thJA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a = 25$  °C.

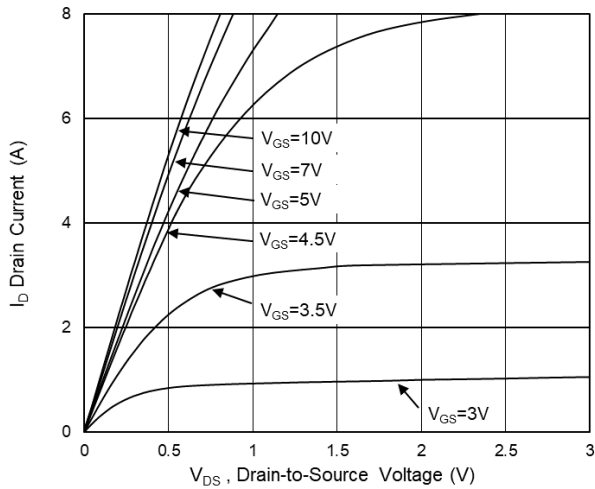
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1	-	3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C	-	-	5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	3.1	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A	-	85	100	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 2 A	-	110	130	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 2 A	-	11	-	S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V, f = 1MHz	-	180	-	pF
Output Capacitance	C <sub>oss</sub>		-	32	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.5	-	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A	-	3.49	-	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	0.66	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	0.92	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	-	3.5	-	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, I <sub>D</sub> = 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 3 Ω	-	4.8	-	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	19	-	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	17	-	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	6	-	
Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)						
Continuous Source Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	3.1	A
Pulsed Source Current	I <sub>SM</sub>		-	-	12	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs	-	13	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>		-	19	-	nC

**Notes**

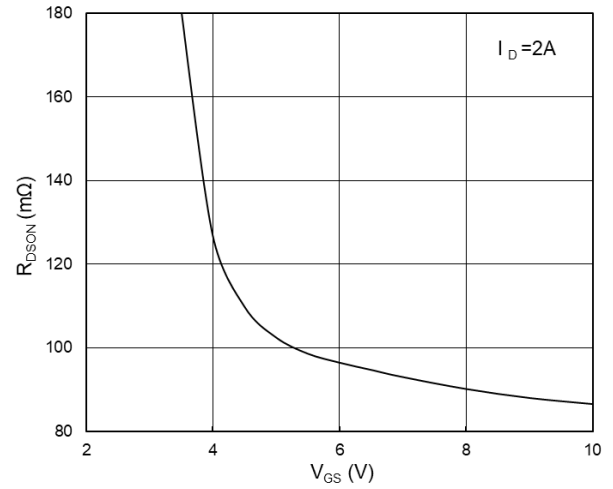
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

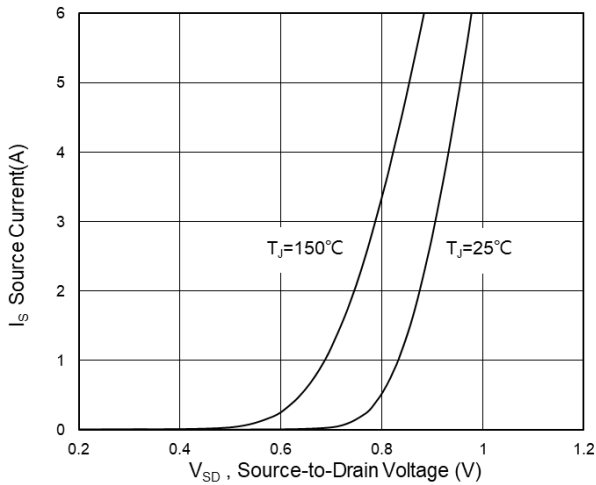
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



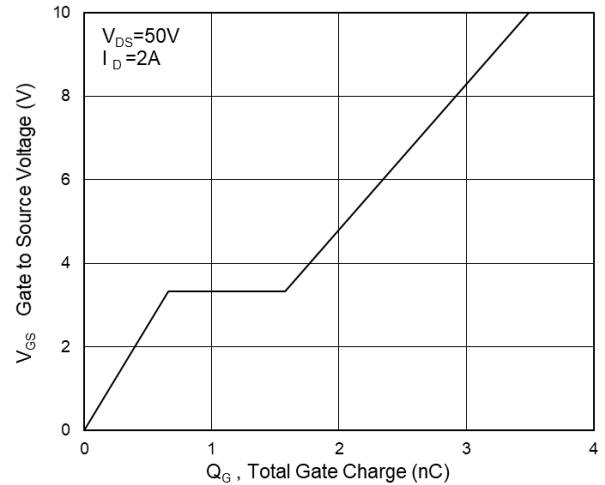
**Typical Output Characteristics**



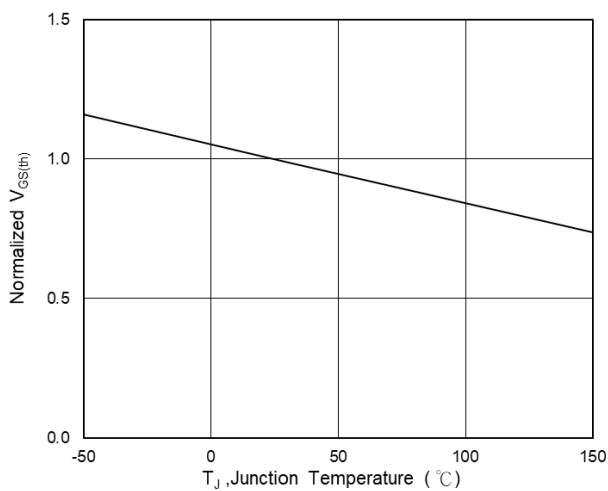
**On-Resistance vs G-S Voltage**



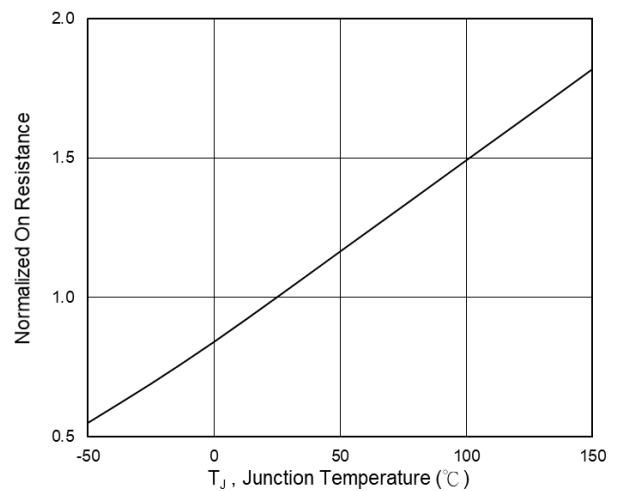
**Source Drain Forward Characteristics**



**Gate-Charge Characteristics**

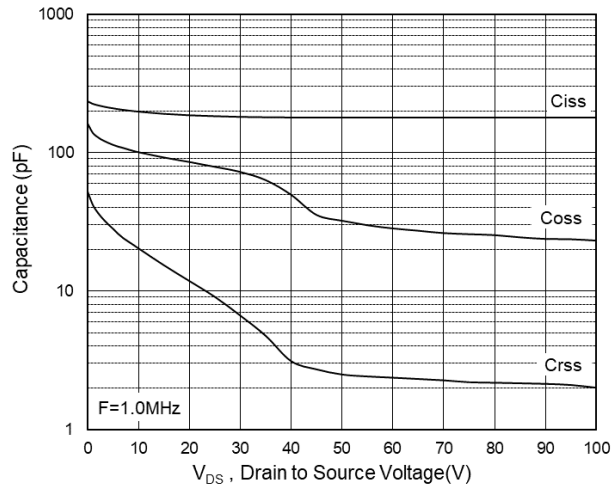


**Normalized  $V_{GS(th)}$  vs  $T_J$**

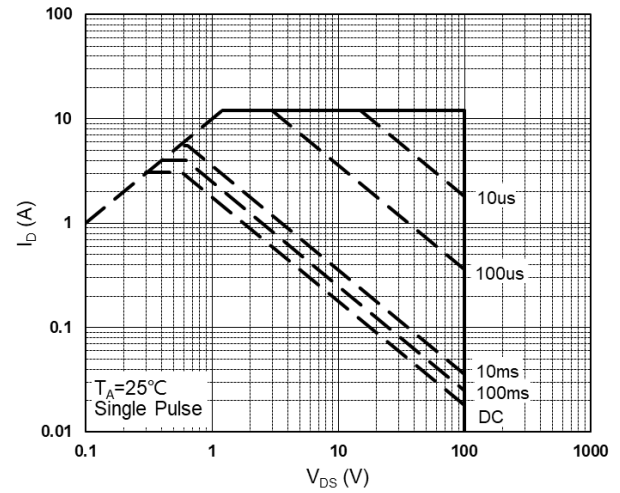


**Normalized  $R_{DS(on)}$  vs  $T_J$**

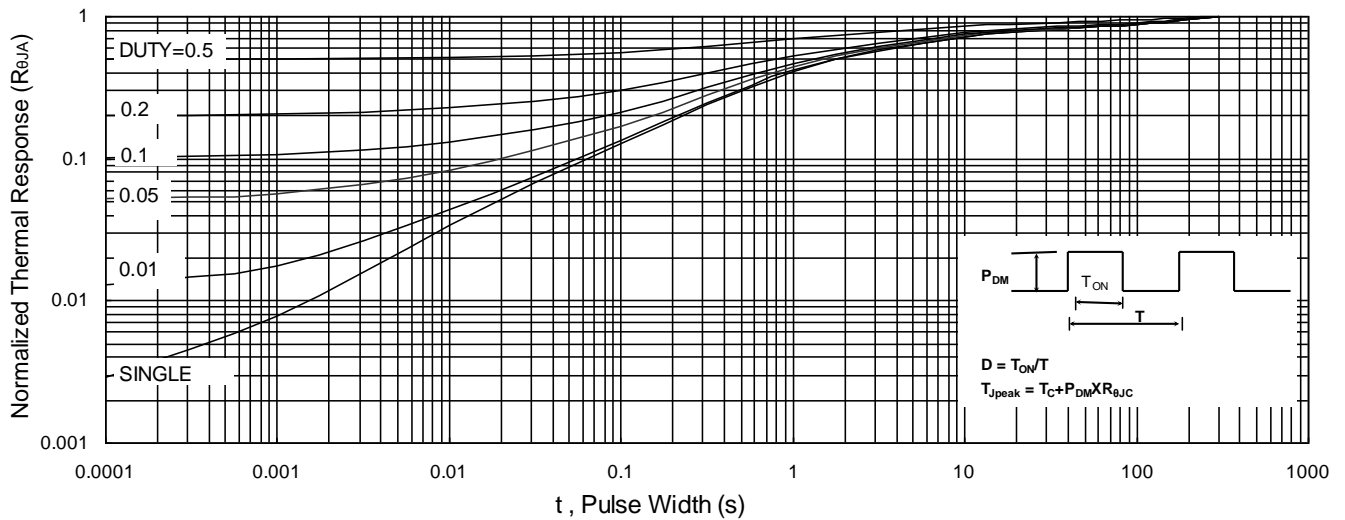
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



**Capacitance**

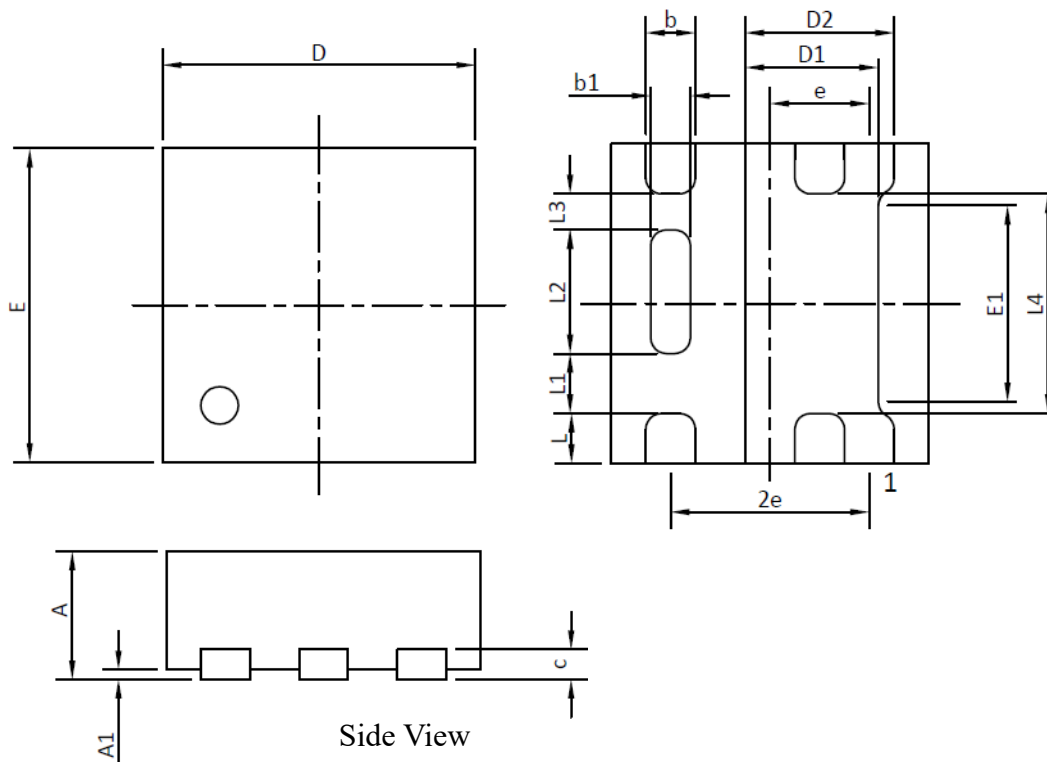


**Safe Operating Area**



**Normalized Maximum Transient Thermal Impedance**

## DFN1.6\*1.6-6L PACKAGE OUTLINE



SYMBOL	Millimeters			Inches		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	-----	0.05	0.000	-----	0.002
b	0.22	0.25	0.28	0.009	0.010	0.011
b1	0.17	0.20	0.23	0.007	0.008	0.009
c	0.152 Ref.			0.006 Ref.		
D	1.55	1.60	1.65	0.061	0.063	0.065
D1	0.67 TYP			0.026 TYP		
D2	0.75 TYP			0.030 TYP		
E	1.55	1.60	1.65	0.061	0.063	0.065
E1	0.98 TYP			0.039 TYP		
e	0.50 BSC			0.020 BSC		
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.25	0.30	0.35	0.010	0.012	0.014
L2	0.57	0.62	0.67	0.022	0.024	0.026
L3	0.13	0.18	0.23	0.005	0.007	0.009
L4	1.05	1.10	1.15	0.041	0.043	0.045

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